Alfa-MOS Technology

AFN3302W

20V N-Channel Enhancement Mode MOSFET

General Description

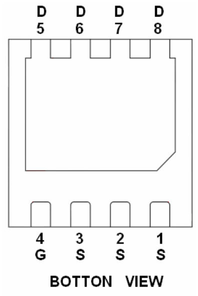
AFN3302W, N-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent $R_{DS(ON)}$, low gate charge.

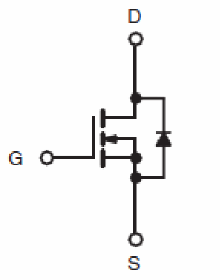
These devices are particularly suited for low voltage power management, such as smart phone and notebook computer and other battery powered circuits, and low in-line power loss are needed in commercial industrial surface mount applications.

Features

- 20V/14A,$R_{DS(ON)}$=14mΩ@V_{GS}=4.5V
- 20V/12A,$R_{DS(ON)}$=18mΩ@V_{GS}=2.5V
- 20V/10A,$R_{DS(ON)}$=26mΩ@V_{GS}=1.8V
- Super high density cell design for extremely low $R_{DS\ (ON)}$
- Exceptional on-resistance and maximum DC current capability
- DFN3X3-8L package design

Pin Description (DFN3X3-8L)





Application

- DC-DC Converter
- POL

Pin Define

Pin	Symbol	Description
1	S	Source
2	S	Source
3	S	Source
4	G	Gate
5	D	Drain
6	D	Drain
7	D	Drain
8	D	Drain

Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFN3302WFN338RG	AFN3302W	DFN3X3-8L	Tape & Reel	5000 EA

※ YY year code
※ MM month code
※ DD date code
※ AFN3302WFN338RG : 13”Tape & Reel ; Pb- Free ; Halogen –Free

Absolute Maximum Ratings

(T_A=25℃ Unless otherwise noted)

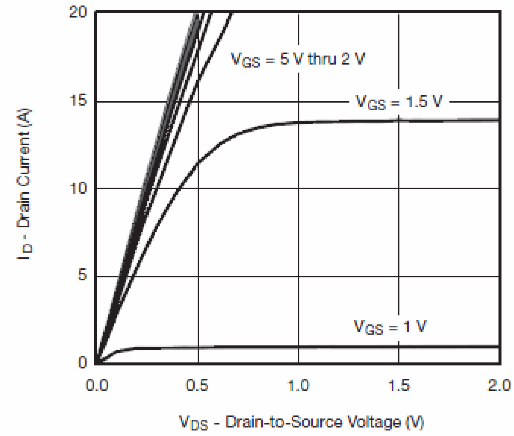
Parameter		Symbol	Typical	Unit
Drain-Source Voltage		V_{DSS}	20	V
Gate –Source Voltage		V_{GSS}	±12	V
Continuous Drain Current(T_J=150℃)	T_A=25℃	I_D	14	A
	T_A=70℃		10	
Pulsed Drain Current		I_{DM}	40	A
Continuous Source Current(Diode Conduction)		I_S	1.6	A
Power Dissipation	T_A=25℃	P_D	36	W
	T_A=70℃		18	
Power Dissipation	T_A=25℃	P_{DSM}	3	W
	T_A=70℃		2	
Operating Junction Temperature		T_J	150	℃
Storage Temperature Range		T_{STG}	-55/150	℃
Thermal Resistance-Junction to Ambient		$R_{\theta JA}$	120	℃/W

Electrical Characteristics

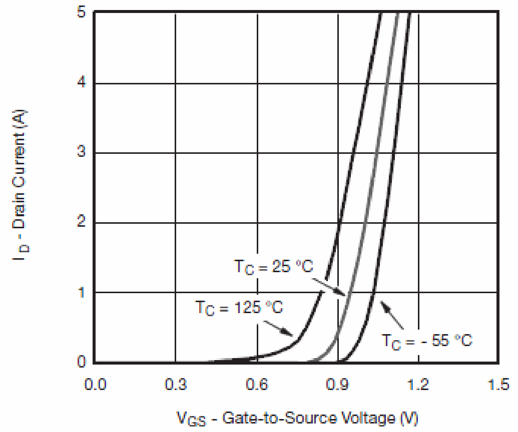
(T_A=25℃ Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V,I_D=250uA	20			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250uA	0.4		1.0	
Gate Leakage Current	I_{GSS}	V_{DS}=0V,V_{GS}=±12V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=16V,V_{GS}=0V			1	uA
		V_{DS}=16V,V_{GS}=0V T_J=85℃			10	
On-State Drain Current	$I_{D(on)}$	V_{DS}≧5V,V_{GS}=10V	40			A
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=4.5V,I_D=14A		11	14	mΩ
		V_{GS}=2.5V,I_D=12A		15	18	
		V_{GS}=1.8V,I_D=10A		20	26	
Forward Transconductance	g_{FS}	V_{DS}=5V,I_D=3.6A		10		S
Diode Forward Voltage	V_{SD}	I_S=1.6A,V_{GS}=0V		0.85	1.5	V
Dynamic						
Total Gate Charge	Q_g	V_{DS}=10V,V_{GS}=4.5V I_D=4.0A		8.2	14	nC
Gate-Source Charge	Q_{gs}			1.2		
Gate-Drain Charge	Q_{gd}			1.0		
Input Capacitance	C_{iss}	V_{DS}=10V,V_{GS}=0V f=1MHz		850		pF
Output Capacitance	C_{oss}			120		
Reverse Transfer Capacitance	C_{rss}			60		
Turn-On Time	$t_{d(on)}$	V_{DD}=10V,R_L=2.2Ω I_D=4.0A,V_{GEN}=4.5V R_G=1Ω		10	16	ns
	t_r			16	25	
Turn-Off Time	$t_{d(off)}$			31	45	
	t_f			10	16	

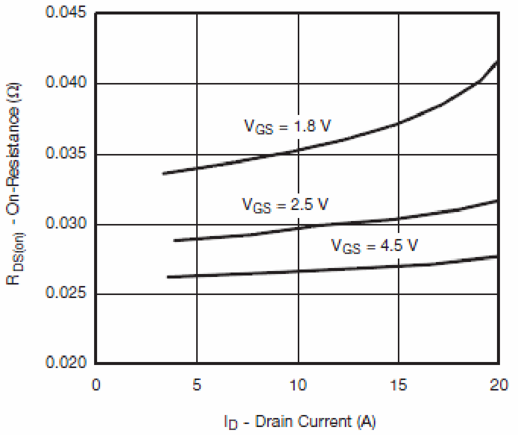
Typical Characteristics



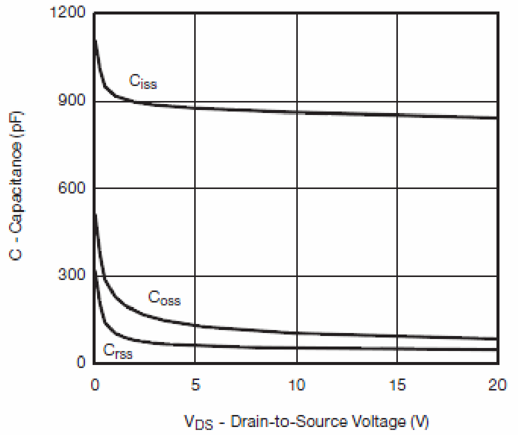
Output Characteristics



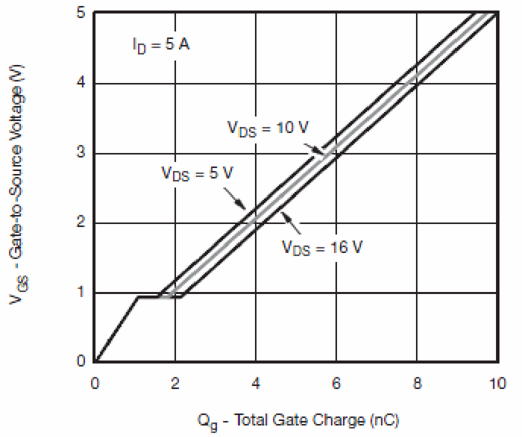
Transfer Characteristics



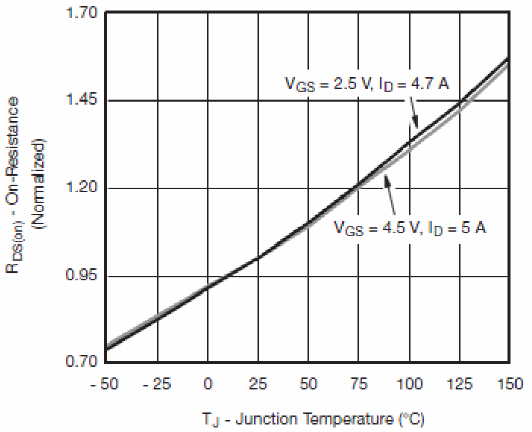
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

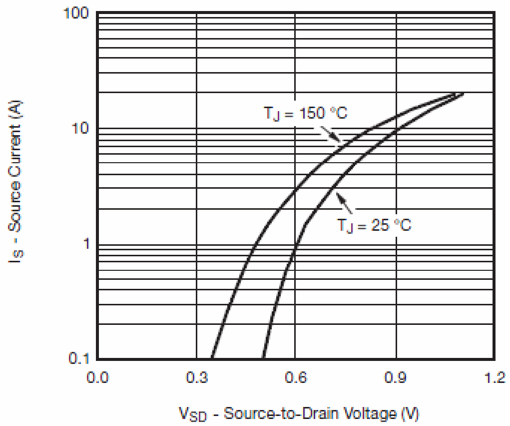


Gate Charge

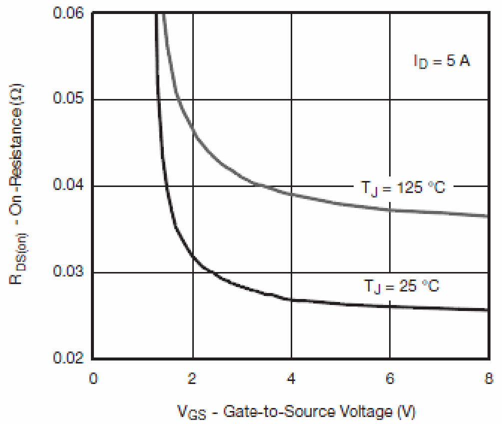


On-Resistance vs. Junction Temperature

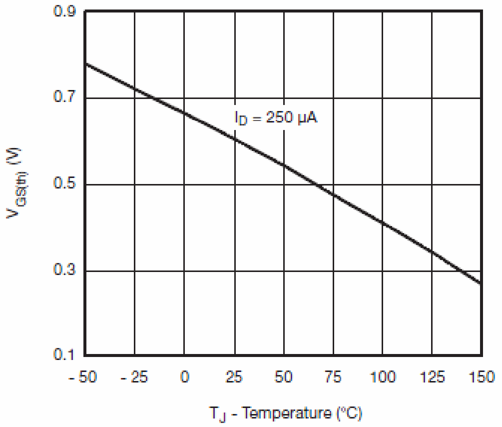
Typical Characteristics



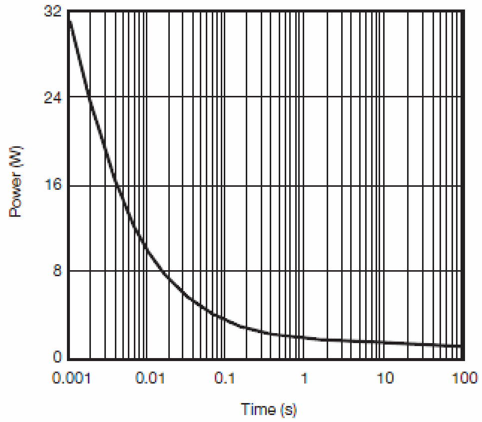
Source-Drain Diode Forward Voltage



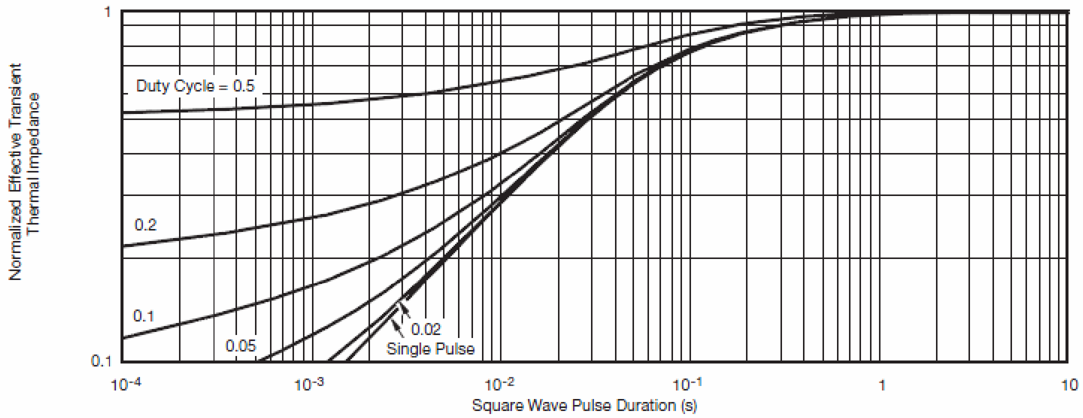
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



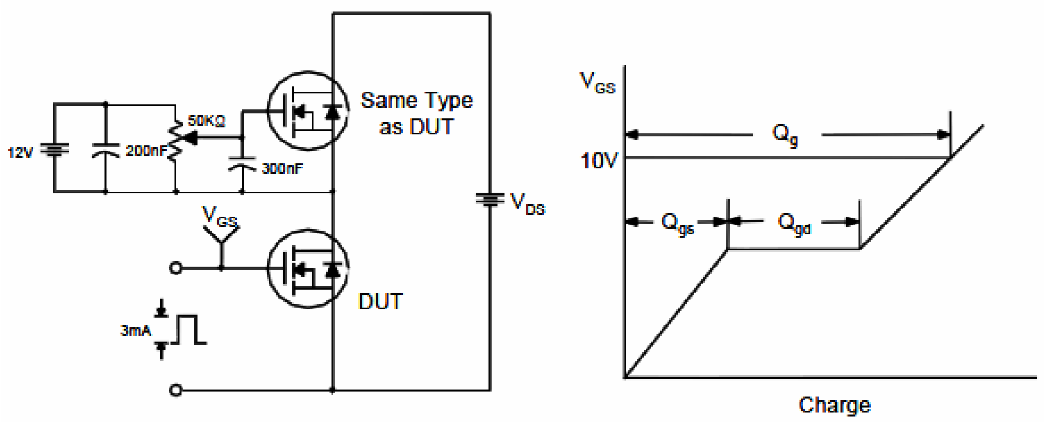
Single Pulse Power (Junction-to-Ambient)



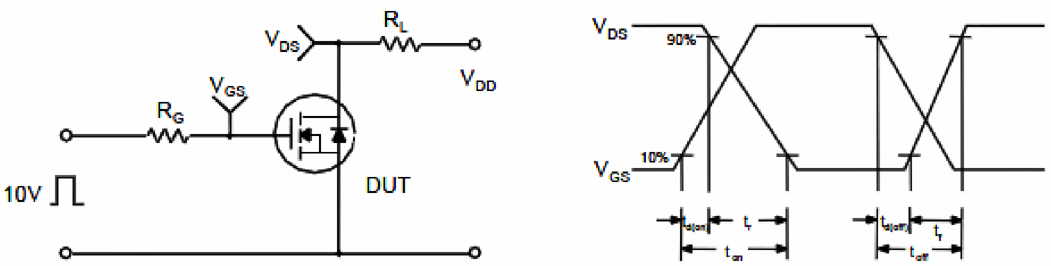
Normalized Thermal Transient Impedance, Junction-to-Foot

Typical Characteristics

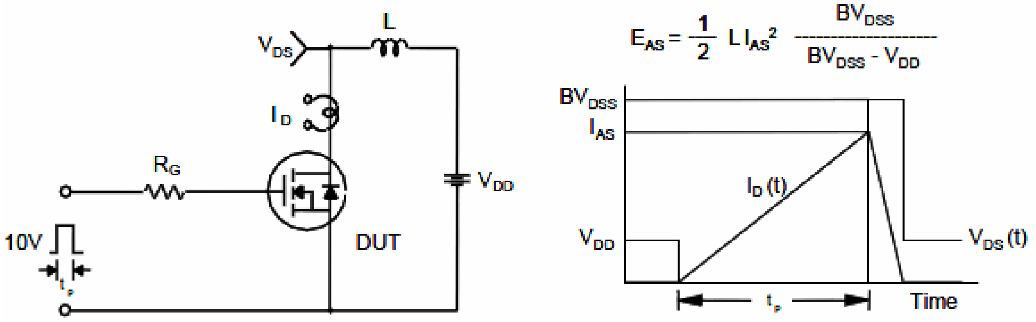
Gate Charge Test Circuit & Waveform



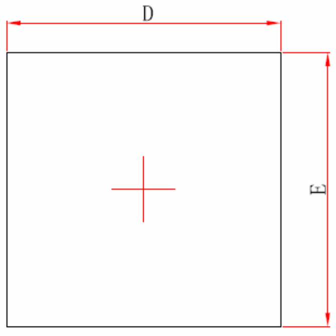
Resistive Switching Test Circuit & Waveforms



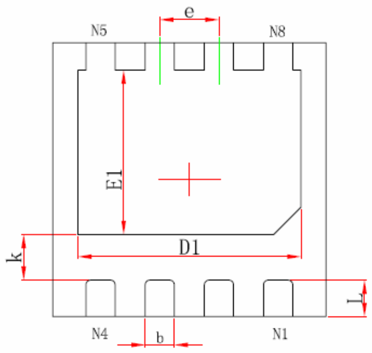
Unclamped Inductive Switching Test Circuit & Waveforms



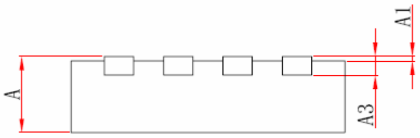
Package Information (DFN3X3-8L)



Top View



Bottom View



Side View

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.800	0.900	0.031	0.035
A1	0.000	0.050	0.000	0.002
A3	0.203REF.		0.008REF.	
D	2.924	3.076	0.115	0.121
E	2.924	3.076	0.115	0.121
D1	2.350	2.550	0.093	0.100
E1	1.700	1.900	0.067	0.075
k	0.450	0.550	0.018	0.022
b	0.270	0.370	0.011	0.015
e	0.650TYP.		0.026TYP.	
L	0.324	0.476	0.013	0.019

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